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Second Generation Platform Technology is designed to meet the growing demands of military communications....

NITRONEX LAUNCHES THERMALLY-ENHANCED POWER TRANSISTOR, NPT1012

Durham, NC (July 29, 2010) - Nitronex, a leader in the design and manufacture of gallium nitride (GaN) based RF solutions for high performance applications in the defense, communications, and industrial & scientific markets, announces the release of the NPT1012, a thermally-enhanced 25W device for applications from DC to 4 GHz. The NPT1012 is the first transistor to be released as part of this second generation platform which was developed to meet the growing demand for wideband, high power and robust RF power amplifiers required by the military communications, jammers and radar market segments.

“The new NPT1012 25W GaN power transistor has been designed specifically to improve broadband power performance by addressing thermal management. Designers can use the NPT1012 transistor to develop compact, multi-octave power amplifiers that simultaneously meet RF and thermal requirements”, stated Gary Blackington, Vice President of Sales and Marketing. “The NPT1012 will be well suited for applications that require wide bandwidth, high efficiency and low thermal resistance. This device will be our second generation 25W discrete GaN RF transistor that has a pedigree of being used in the most highly advanced and widely used tactical radios in the world.”

“Thermal optimization requires attacking the problem from every angle. We made improvements in the full thermal stack from the die itself to packaging and assembly,” said Ray Crampton, Vice President of Engineering. “With these enhancements, we achieved a 25% reduction in thermal rise in our customers’ applications.”

The NPT1012 provides more than 20W of output power and over 50% drain efficiency in a broadband application circuit across 1 to 2.5 GHz. It is available in a thermally-enhanced air cavity bolt-down package, is lead-free and RoHS compliant. The NPT1012 is now available in production quantities from stock to 16 weeks lead time through Nitronex's standard sales channels.

About Nitronex

Nitronex Corporation is an innovative leader in the design and manufacture of gallium nitride (GaN) based RF solutions. Nitronex is the pioneer in developing high performance gallium nitride on silicon (GaN-on-Si) semiconductor solutions using its proprietary SIGANTIC® manufacturing process. Nitronex products enable high performance applications in the defense, communications, and industrial & scientific markets. An ISO-9001 certified manufacturer, Nitronex was founded in 1999 and is headquartered in Durham, NC. Nitronex holds 24 patents with 15 others pending. For more information, please visit the Nitronex web site at www.nitronex.com.

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